

U.S. Department of Commerce, Patent and Trademark Office				Atty Docket No.		Serial No.	
NOV 09 2004				M-15222 US		10/632,155	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Applicant			
(Use several sheets if necessary)				Yi Ding			
				Filing Date		Group	
				July 30, 2003		2818	
U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
DA	AA	6,265,739	Jul. 2001	Yaegashi et al.			
	AB	6,747,310	Jun. 2004	Fan et al.			
	AC	2003/0205776	Nov. 2003	Yaegashi et al.			
	AD	6,468,865	Oct. 2002	Yang et al.			
	AE	6,218,689	Apr. 2001	Chang et al.			
	AF	6,214,669	Apr. 2001	Hisamune			
	AG	6,162,682	Dec. 2000	Kleine			
	AH	6,232,185	May-01	Wang			
	AI	5,912,843	Jun. 1999	Jeng			
	AJ	6,436,764	Aug. 2002	Hsieh			
	AK	6,344,993	5 Feb. 2002	Harari et al.			
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	AM	6,355,524	Mar. 2002	Tuan et al.			
	AN	6,696,340	Feb. 2004	Furuhata			
	AO	5,705,415	Jan. 1998	Orlowski et al.			
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Examiner		Date Considered		3/23/05			
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U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>Pa</i>	AA	5,445,983	Aug. 1995	Hong			
	AB	5,910,912	Jun. 1999	Hsu et al.			
	AC	5,918,124	Jun. 1999	Sung			
	AD	6,040,216	Mar. 2000	Sung			
	AE	6,107,141	Aug. 2000	Hsu et al.			
	AF	6,133,098	Oct. 2000	Ogura et al.			
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	AK	6,566,196	May-03	Haselden et al.			
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Examiner <i>SWR</i>		Date Considered <i>9/26/05</i>					
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July 30, 2003					Unassigned			
U.S. Patent Documents								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
<i>DL</i>	AA	6,420,231	16 Jul. 2002	Harari et al.	438	257		
<i>DL</i>	AB	2003/0218908 A1	27 Nov. 2003	Park et al.				
<i>DL</i>	AC	2004/0004863 A1	8 Jan. 2004	Wang				
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	AH							
Foreign Patent Documents								
							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
<i>DL</i>	AI	EP 0 938 098 A2	25 Aug. 1999	Europe				
	AJ							
	AK							
	AL							
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)								
<i>DL</i>	AM	United States Patent Application No. 10/798,475, entitled "Fabrication of Conductive Lines Interconnecting Conductive Gates in Nonvolatile Memories and Non-Volatile Memory Structures," Filed on March 10, 2004; Attorney Docket No. M-15296 US.						
<i>DL</i>	AN	United States Patent Application No. 10/797,972, entitled "Fabrication of Conductive Lines Interconnecting First Conductive Gates in Nonvolatile Memories Having Second Conductive Gates Provided By Conductive Gates Lines, Wherein The Adjacent Conductive Gate Lines For The Adjacent Columns Are Spaced From Each Other, And Non-Volatile Memory Structures," Filed on March 10, 2004; Attorney Docket No. M-15297 US.						
	AO							
	AP							
Examiner		<i>DL</i>						
Date Considered		3/23/05						
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